



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	$R_{DS(on)}$ Max	$I_{D Max}$ $T_A = +25^\circ C$
-50V	$10\Omega @ V_{GS} = -5V$	-130mA

Description and Applications

This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- General Purpose Interfacing Switch
- Power Management Functions
- Analog Switch

Features and Benefits

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed

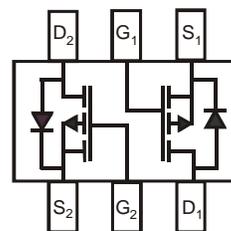
Mechanical Data

- Case: SOT363
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish Annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Weight: 0.006 grams (Approximate)

SOT363 (Standard)



Top View



Top View
Internal Schematic

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-50	V
Drain-Gate Voltage (Note 5)	V _{DGR}	-50	V
Gate-Source Voltage	V _{GSS}	±20	V
Drain Current (Note 6)	I _D	-130	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P _D	300	mW
Thermal Resistance, Junction to Ambient	R _{θJA}	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV _{DSS}	-50	-75	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = +25°C
		—	—	-2	μA	V _{DS} = -50V, V _{GS} = 0V, T _J = +125°C
		—	—	-100	nA	V _{DS} = -25V, V _{GS} = 0V, T _J = +25°C
Gate-Body Leakage	I _{GSS}	—	—	±10	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V _{GS(th)}	-0.8	-1.6	-2.0	V	V _{DS} = V _{GS} , I _D = -1mA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	6	10	Ω	V _{GS} = -5V, I _D = -0.1A
Forward Transconductance	g _{FS}	0.05	—	—	S	V _{DS} = -25V, I _D = -0.1A
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	—	45	pF	V _{DS} = -25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	—	25	pF	
Reverse Transfer Capacitance	C _{rss}	—	—	12	pF	
SWITCHING CHARACTERISTICS (Note 8)						
Turn-On Delay Time	t _{d(ON)}	—	10	—	ns	V _{DD} = -30V, I _D = -0.27A, R _{GEN} = 50Ω, V _{GS} = -10V
Turn-Off Delay Time	t _{d(OFF)}	—	18	—	ns	

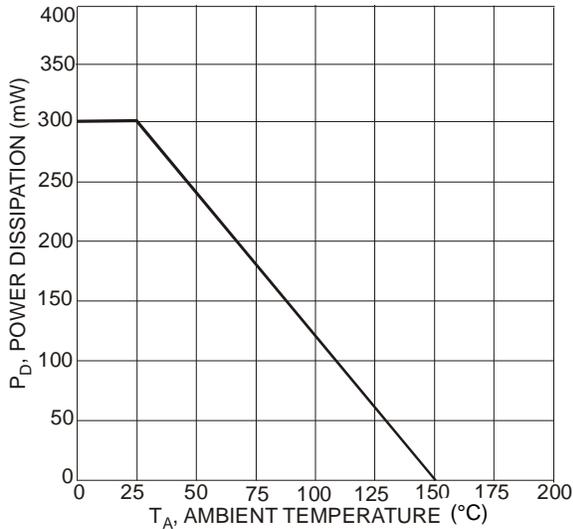


Fig. 1 Max Power Dissipation vs. Ambient Temperature

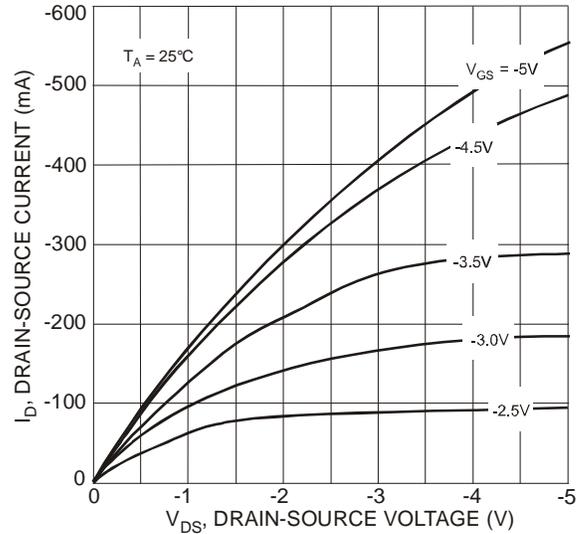


Fig. 2 Drain-Source Current vs. Drain-Source Voltage

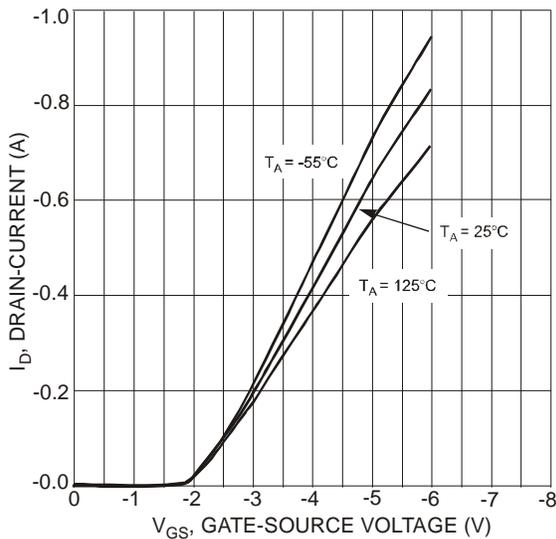


Fig. 3 Drain-Current vs. Gate-Source Voltage

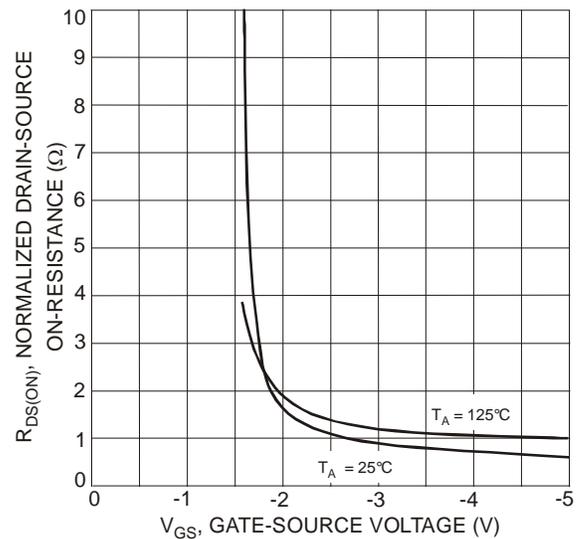


Fig. 4 On-Resistance vs. Gate-Source Voltage

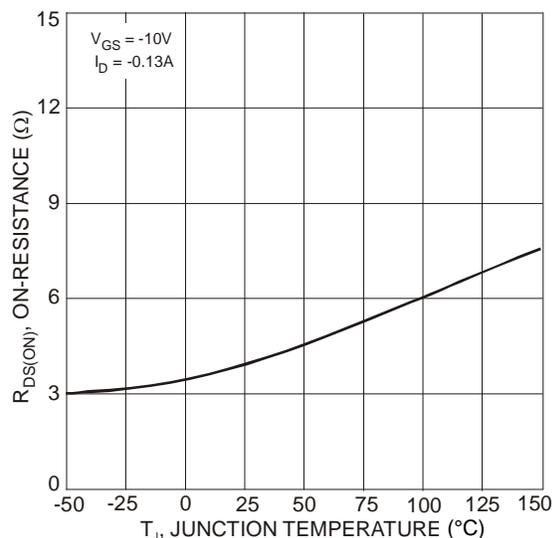


Fig. 5 On-Resistance vs. Junction Temperature

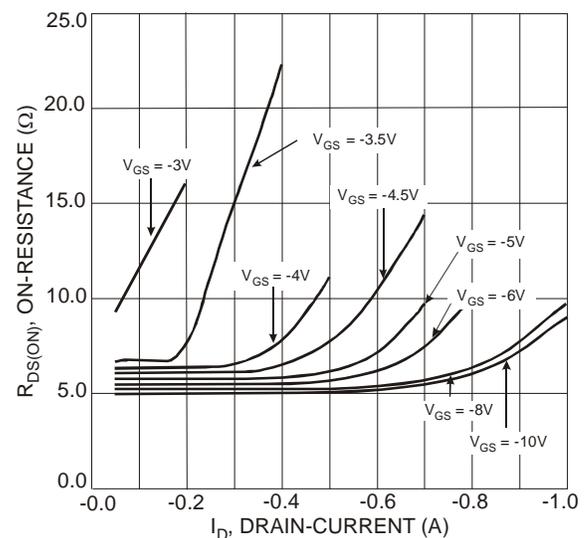
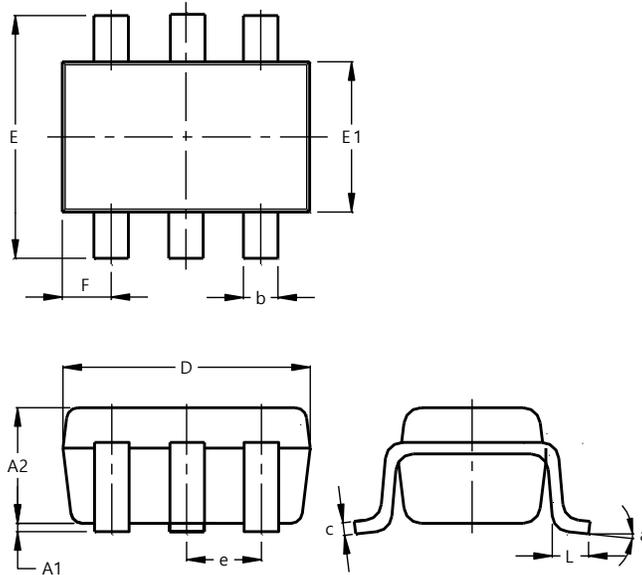


Fig. 6 On-Resistance vs. Drain-Current

Package Outline Dimensions

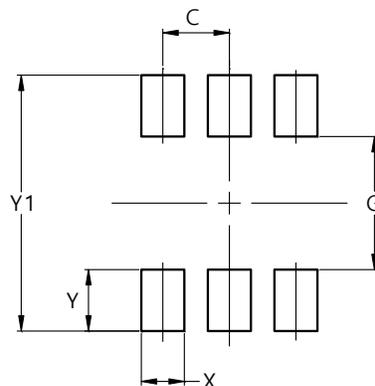
SOT363 (Standard)



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Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.80	1.00	0.90
b	0.10	0.35	0.225
c	0.08	0.22	0.15
D	1.80	2.20	2.00
E	2.00	2.45	2.225
E1	1.15	1.35	1.25
e	--	--	0.65
F	0.25	0.45	0.35
L	0.25	0.46	0.355
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

SOT363 (Standard)



Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500